

**1N55**  
**GOLD BONDED GERMANIUM DIODE**

**FEATURES**

Low forward voltage drop—low power consumption  
 Thirty years of proven reliability—one million hours mean time between failures (MTBF)  
 Very low noise level  
 Metallurgically bonded

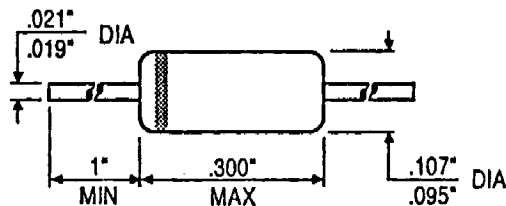
**ABSOLUTE MAXIMUM RATINGS** (at 25 °C, unless otherwise specified)

Peak Inverse Voltage 150 Volts  
 Peak Forward Current 500 mA  
 Operating Temperature Range - 65 °C to 85 °C  
 Average Power Dissipation 80 mW

**ELECTRICAL CHARACTERISTICS**

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	150		V	25 °C
Reverse Current	I <sub>r</sub>	150 V		800	μA	25 °C
Forward Voltage	V <sub>f</sub>	3 mA		1	V	25 °C

**MECHANICAL**



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